

What is claimed is:

1. A thin film depositing method comprising the steps of:
 - placing a substrate in a chamber;
 - causing a gas to flow into said chamber to heat said substrate through heat exchange with said gas;
 - evacuating said chamber; and
 - depositing a film on a surface of said substrate heated in said chamber.
2. A thin film depositing method comprising the steps of:
 - placing a substrate in a heating chamber;
 - causing a first gas to flow into said heating chamber to heat said substrate through heat exchange with said first gas;
 - moving said substrate to a deposition chamber, evacuating said deposition chamber, and then supplying a second gas into said deposition chamber; and
 - causing an electrical discharge in said second gas such that said second gas decomposes into components which adhere to a surface of said substrate to deposit a film thereon,
 - wherein said first gas is a gas from which moisture and organic substances have been removed.
3. The thin film depositing method according to claim 2, wherein said first gas is an inert gas.
4. The thin film depositing method according to claim 2, wherein said first gas is nitrogen gas.
5. A thin film depositing apparatus comprising:
 - a chamber;

a substrate placed in said chamber;
a gas which flows inside said chamber to heat said substrate through heat exchange with said gas; and
a pumping system which evacuates said chamber;
whereby a film is deposited on a surface of said substrate in said chamber.

6. A thin film depositing apparatus comprising:

a heating chamber;
a substrate placed in said heating chamber;
a gas which flows inside said heating chamber to heat said substrate through heat exchange with said gas; and
a deposition chamber in which a film is deposited on a surface of said substrate, said deposition chamber being located downstream of and connected to said heating chamber through a valve,
wherein said gas is a gas from which moisture and organic substances have been removed.

7. The thin film depositing apparatus according to claim 6, wherein said gas is an inert gas.

8. The thin film depositing apparatus according to claim 6, wherein said gas is nitrogen gas.

9. The thin film depositing apparatus according to claim 6, further comprising a compression cooler which removes moisture and organic substances from said gas.

10. The thin film depositing apparatus according to claim 6, further comprising a filter device which removes moisture and organic substances from said gas.